# Green Journals

International Approved Journals

## Journal Information

| | |
|---|---|
| **Journal Title** | IEEE TRANSACTIONS ON DEVICE AND MATERIALS RELIABILITY |
| **Publisher** | IEEE |
| **ISSN** | 1530-4388 |
| **E-ISSN** | 1558-2574 |
| **Database** | Clarivate |
| **Domain** | Physical Sciences, Social Sciences |

## Classification History

| Year | A+ | A | B | C |
|---|---|---|---|---|
| **2026** | | ✓ | ✓ | |
| **2025** | | ✓ | ✓ | |
| **2024** | | ✓ | ✓ | |
| **2023** | | ✓ | ✓ | |
| **2021/2022** | | ✓ | ✓ | |
| **2020** | | ✓ | ✓ | |
| **2019** | | ✓ | ✓ | |
| **2018** | | ✓ | | |

**Classification:** The table above shows all journal classifications recorded for each classification year in the Green Journals database. A journal may have more than one classification in the same year.

## Recent Articles

**Electrical Behavior at Cryogenic Temperature of the Radiation-Tolerant Hourglass MOS Transistor**
2026-9 Vol. 26 Issue 3 Pages 807-814
Authors: Carlos Alfredo Pelcastre Ortega, Mónico Linares Aranda, Daniel Ferrusca Rodríguez et al.
DOI: 10.1109/tdmr.2026.3701856

**Influence of Gate Insulator Modulation on the Electrical and Material Properties of Dual-Gate InGaZnO Thin-Film Transistors**
2026-9 Vol. 26 Issue 3 Pages 880-887
Authors: Ya-Ting Chien, Yu-An Chen, Bo-Shen Huang et al.
DOI: 10.1109/tdmr.2026.3712375

**Field- and Temperature-Induced Drift in Multi-Level Al-Doped HfO <sub>2</sub> RRAM**
2026-9 Vol. 26 Issue 3 Pages 871-879
Authors: Andrea Baroni, Jianan Wen, Eduardo Pérez et al.
DOI: 10.1109/tdmr.2026.3700862

**Investigation of AlSb Monolayer and Its Application in Single-Electron Transistor for Low-Power Switching and Toxic Gas Sensing**
2026-9 Vol. 26 Issue 3 Pages 942-951
Authors: Prity Sinha, Pramod Kumar Tiwari
DOI: 10.1109/tdmr.2026.3706183

**Modeling and Evaluation of Single Event Effects on Hafnia-Based FeRAM**
2026-9 Vol. 26 Issue 3 Pages 849-857
Authors: Stuart E. Wodzro, Shimeng Yu
DOI: 10.1109/tdmr.2026.3696237

**Reliability-Assisted Electro-Physical Modeling of Radiation-Induced Resistance Fluctuation in Nanosheet FET**
2026-9 Vol. 26 Issue 3 Pages 832-838
Authors: Khushi Jain, Sandeep Kumar, Sunil Rathore et al.
DOI: 10.1109/tdmr.2026.3713056

**3D NAND Scaling Performance Enhancement Using 2D MoS <sub>2</sub> Channel**
2026-9 Vol. 26 Issue 3 Pages 815-821
Authors: Mohd Ashraf Lone, Dibyadrasta Sahoo, Sanjeev Kumar Manhas
DOI: 10.1109/tdmr.2026.3697549

**Reliability-Aware Structural and Spacer Optimization of E-Shaped CombFET for Advanced CMOS Nodes**
2026-9 Vol. 26 Issue 3 Pages 897-905
Authors: B. Pavithara, P. Prithvi
DOI: 10.1109/tdmr.2026.3713133

**Influence of Epitaxial Layer Thickness on the Holding Voltage Scalability of Bi-Directional SCR Devices**
2026-9 Vol. 26 Issue 3 Pages 794-799
Authors: Ting Yang, Jie Zeng, Qidong Xie et al.
DOI: 10.1109/tdmr.2026.3698068

**Effect of Transistor and Interconnect Scaling on Aging in Advanced SRAM**
2026-9 Vol. 26 Issue 3 Pages 917-926
Authors: Zhe Zhang, Mahta Mayahinia, Christian Weis et al.
DOI: 10.1109/tdmr.2026.3693656